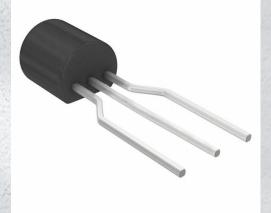


TIS97_D74Z Datasheet

www.digi-electronics.com



DiGi Electronics Part Number	TIS97_D74Z-DG
Manufacturer	onsemi
Manufacturer Product Number	TIS97_D74Z
Description	TRANS NPN 40V 0.5A TO92-3
Detailed Description	Bipolar (BJT) Transistor NPN 40 V 500 mA 625 mW T hrough Hole TO-92-3

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
TIS97_D74Z	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	500 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
40 V	
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
10nA (ICBO)	250 @ 100μA, 5V
Power - Max:	Frequency - Transition:
625 mW	
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-226-3, TO-92-3 (TO-226AA) Formed Leads	TO-92-3
Base Product Number:	
TIS97	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.21.0095



NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Symbol Parameter		Units
V_{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

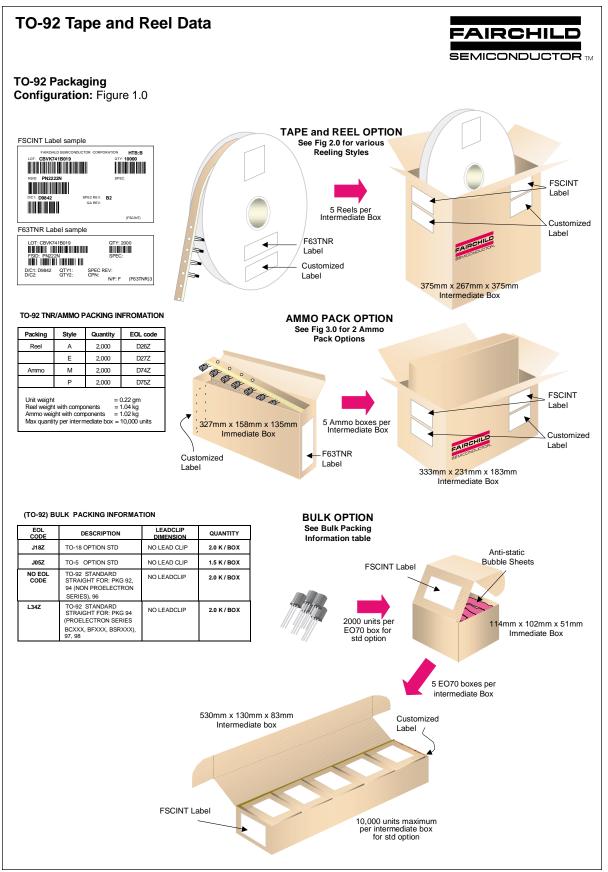
Thermal Characteristics

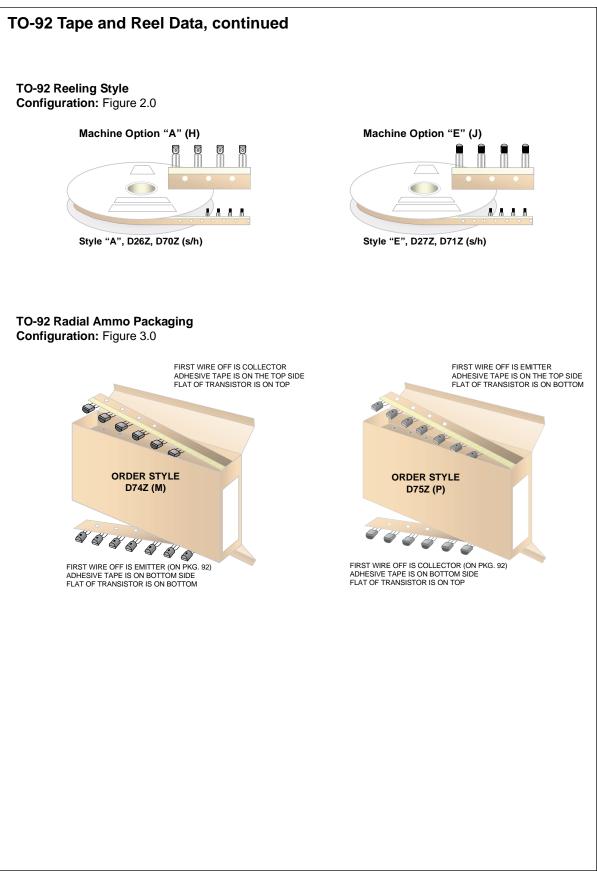
Thermal Characteristics TA = 25°C unless otherwise noted			
Symbol	Characteristic	Max	Units
		TIS97	
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta_{JC}}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

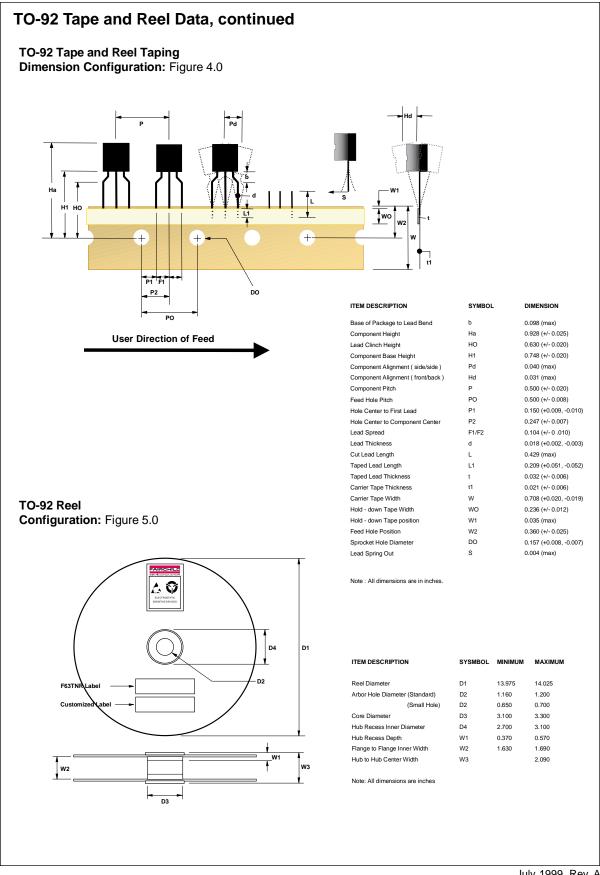
© 1997 Fairchild Semiconductor Corporation

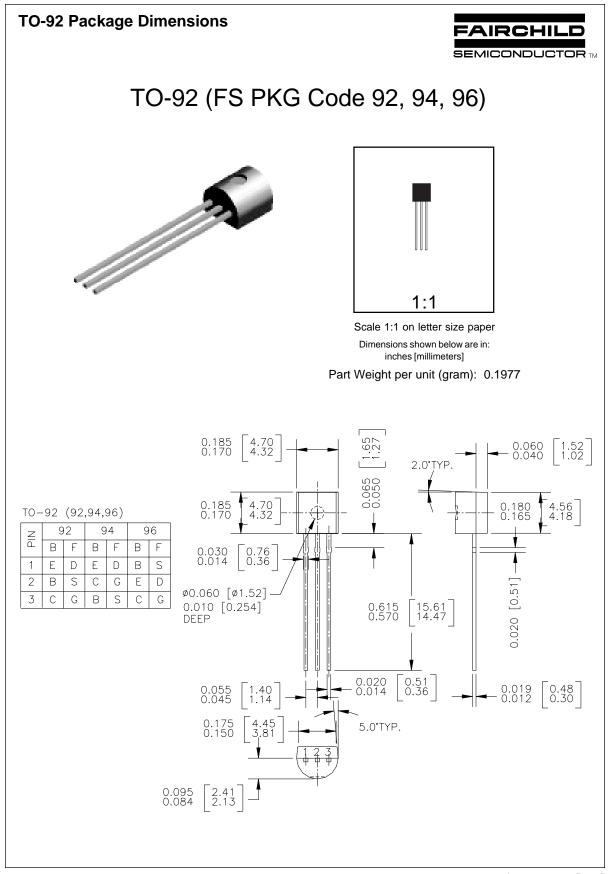
NPN General Purpose A					(continued	
Electr	ical Characteristics	= 25°C unless otherwise noted		1	•	
Symbol	Parameter	Test Conditions	Min	Max	Units	
OFF CHA	RACTERISTICS					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	40		V	
сво	Collector Cutoff Current	$V_{CB} = 40 V, I_E = 0$ $V_{CB} = 60 V, I_E = 0$		10 10	nA μA	
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 6.0 \text{ V}, I_{C} = 0$		20	nA	
	RACTERISTICS*				1	
ON CHAF		$V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$ $V_{CE} = 5.0 V, I_C = 100 \mu\text{A}$	250 0.45	700	V	
ON CHAR ^h FE V _{BE(on)}	RACTERISTICS*	V _{CE} = 5.0 V, I _C = 100 μA			V	
ON CHAR D _{FE} V _{BE(on)}	ACTERISTICS* DC Current Gain Base-Emitter On Voltage	V _{CE} = 5.0 V, I _C = 100 μA			V PF	
ON CHAF ^{TFE} VBE(ON) SMALL S Ccb	ACTERISTICS* DC Current Gain Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}$ $V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}$	0.45	0.65		
ON CHAR NFE VBE(ON) SMALL S	ACTERISTICS* DC Current Gain Base-Emitter On Voltage IGNAL CHARACTERISTICS Collector-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$ $V_{CE} = 5.0 \text{V}, I_{C} = 100 \mu\text{A}$ $V_{CB} = 5.0 \text{V}, f = 1.0 \text{MHz}$ $V_{EB} = 0.5 \text{V}, f = 1.0 \text{MHz}$ $I_{C} = 100 \mu\text{A}, V_{CE} = 5.0 \text{V}, f = 1.0 \text{kHz}$	0.45	4.0	pF	
ON CHAF ^T FE ^J BE(on) SMALL S Cob Cob Cob Cob Cob Cob Cob	ACTERISTICS* DC Current Gain Base-Emitter On Voltage IGNAL CHARACTERISTICS Collector-Base Capacitance Emitter-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$ $V_{CE} = 5.0 \text{V}, I_C = 100 \mu\text{A}$ $V_{CB} = 5.0 \text{V}, I_C = 100 \mu\text{A}$ $V_{EB} = 0.5 \text{V}, f = 1.0 \text{MHz}$ $I_C = 100 \mu\text{A}, V_{CE} = 5.0 \text{V},$ $f = 1.0 \text{Hz}$ $I_C = 10 \text{mA}, V_{CE} = 5.0 \text{V},$ $f = 100 \text{MHz}$	0.45 1.0	0.65 4.0 16	pF	
DN CHAF PFE VBE(ON) SMALL S Cob Cob Cob	ACTERISTICS* DC Current Gain Base-Emitter On Voltage IGNAL CHARACTERISTICS Collector-Base Capacitance Emitter-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$ $V_{CE} = 5.0 \text{V}, I_C = 100 \mu\text{A}$ $V_{CB} = 5.0 \text{V}, I_C = 100 \mu\text{A}$ $V_{EB} = 0.5 \text{V}, f = 1.0 \text{MHz}$ $I_C = 100 \mu\text{A}, V_{CE} = 5.0 \text{V},$ $f = 1.0 \text{kHz}$ $I_C = 10 \text{mA}, V_{CE} = 5.0 \text{V},$	1.0 250	0.65 4.0 16	pF	

TIS97









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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

SuperSOT[™]-6

SuperSOT[™]-8

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.
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